

a plurality of source diffusion layers formed in a first line contact region located at a first side of the word line region;

a plurality of source diffusion layers formed in a second line contact region located at a second side of the word line region; and

a plurality of line contact patterns formed in the first and second line contact regions, <sup>(crossing)?</sup>

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wherein the line contact patterns formed in the first line contact region and the line contact patterns formed in the second line contact region are alternately positioned, and current for measuring a resistance flows along the first line contact region and the second line contact region between the word line in three dimensions.

2.(Amended) The test pattern according to claim 1, wherein the word line region, the first line contact region, and the second line contact region are juxtapositioned.

3.(Amended) The test pattern according to claim 1, wherein the source diffusion layer in the first line contact region and the source diffusion layer in the second line contact region are electrically connected by an interconnection diffusion layer in the word line region.

4.(Amended) The test pattern according to claim 1, wherein one of the plurality of line contact patterns in the first line contact region electrically connects two of the

plurality of source diffusion layers in the first line contact region and is electrically isolated from another one of the plurality of line contact patterns. *1 1 2 ? current flows*

5.(Amended) The test pattern according to claim 1, wherein one of the plurality of line contact patterns in the second line contact region electrically connects two of the plurality of source diffusion layers in the second line contact region, and is electrically isolated from another one of the plurality of line contact patterns. *1 1 2 ? current flows*

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6.(Amended) A method of manufacturing a test pattern for measuring a contact resistance, comprising:

forming a plurality of device isolation *areas* (films) in a test wafer to define a plurality of active regions;

simultaneously forming a plurality of source diffusion layers in ones of the plurality of active regions of a first line contact region, a plurality of interconnection diffusion layers in ones of the plurality of active regions of a word line, and a plurality of source diffusion layers in ones of the plurality of active regions of a second line contact region;

forming a word line surrounded by an insulating film spacer in the word line region;

forming an insulating layer on an entire structure including the word line, the insulating layer having a flattened surface;

forming a self-aligned contact mask on the insulating layer; and

forming a plurality of line contact patterns in the first and second line contact regions through a self-aligned contact process using the self-aligned contact mask,

wherein the line contact pattern formed in the first line contact region and the line contact pattern formed in the second line contact region are alternatingly positioned, and current for measuring a resistance flows along the first line contact region and the second line contact region between the word line in three dimensions.

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7.(Amended) The method according to claim 6, wherein the word line region, the first line contact region, and the second line contact region are juxta-positioned crossing the plurality of device isolation <sup>area</sup> (films) and the plurality of active regions.

8.(Amended) The method according to claim 6, wherein one of the plurality of source diffusion layers in the first line contact region and one of the plurality of the source diffusion layers in the second line contact region are electrically connected by one of the plurality of interconnection diffusion layers in the word line region.

9.(Amended) The method according to claim 6, wherein one of the plurality of line contact patterns in the first line contact region electrically connects two of the plurality of source diffusion layers in the first line contact region and is electrically isolated from another one of the plurality of line contact patterns.

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10.(Amended) The method according to claim 6, wherein one of the plurality of line contact patterns in the second line contact region electrically connects two of the plurality of source diffusion layers in the second line contact region, and is electrically isolated from another one of the plurality of line contact patterns. 112 current flows

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11.(Amended) The method according to claim 6, wherein the self-aligned contact mask is formed to cover an upper portion of the word line, an upper portion of the device isolation film between a first one of the plurality of source diffusion layers and a second one of the plurality of source diffusion layers in the first line contact region, and an upper portion of the device isolation film between the second one of the plurality of source diffusion layers and a third one of the plurality of source diffusion layers in the second line contact region.

12.(Amended) A method of manufacturing a test pattern for measuring a contact resistance, comprising:

forming a plurality of device isolation films <sup>on wafer</sup> in a test wafer to define a plurality of active regions;

forming a threshold voltage ion implantation region in the plurality of ~~the~~ active regions in a word line region;

forming a word line in the word line region;

forming a plurality of source diffusion layers in each of the plurality of active regions of a first line contact region;

forming a plurality of source diffusion layers in each of the plurality of active regions of a second line contact region;

forming an insulating film spacer surrounding the word line;

forming an insulating layer on an entire structure including the word line, the insulating layer having a flattened surface;

forming a self-aligned contact mask on the insulating layer; and

forming a plurality of line contact patterns in the first and second line contact regions through a self-aligned contact process using the self-aligned contact mask,

wherein the line contact pattern formed in the first line contact region and the line contact pattern formed in the second line contact region are alternatingly positioned, and current for measuring a resistance flows along the first line contact region and the second line contact region between the word line in three dimensions.

13.(Amended) The method according to claim 12, wherein the word line region, the first line contact region, and the second line contact region are juxtapositioned crossing the plurality of device isolation films and the plurality of active regions.

14.(Amended) The method according to claim 12, wherein the plurality of source diffusion layers in the first line contact region and the plurality of source diffusion layers in the second line contact region are electrically connected by a channel formed in the threshold voltage ion implantation region by applying a voltage to the word line in the word line region.

15.(Amended) The method according to claim 12, wherein one of the plurality of line contact patterns in the first line contact region electrically connects two of the plurality of source diffusion layers in the first line contact region, and is electrically isolated from another one of the plurality of line contact patterns.

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16.(Amended) The method according to claim 12, wherein one of the plurality of line contact patterns in the second line contact region electrically connects two of the plurality of source diffusion layers in the second line contact region, and is electrically isolated from another one of the plurality of line contact patterns.

17.(Amended) The method according to claim 12, wherein the self-aligned contact mask is formed to cover an upper portion of the word line, an upper portion of the device isolation <sup>area</sup> film between a first one of the plurality of source diffusion layers and a second one of the plurality of source diffusion layers in the first line contact region, and an upper portion of the device isolation <sup>area</sup> film between the second one of the plurality of source diffusion layers and a third one of the plurality of source diffusion layers in the second line contact region.

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